

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

MCH3479 — General-Purpose Switching Device Applications

Features

- ON-resistance RDS(on)1=49m Ω (typ.)
- · 1.8V drive
- · Halogen free compliance
- · Protection diode in

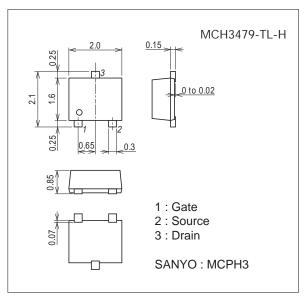
Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		20	V
Gate-to-Source Voltage	V _{GSS}		±12	V
Drain Current (DC)	ID		3.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	14	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm ² ×0.8mm)	0.9	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Package Dimensions

unit : mm (typ) 7019A-003

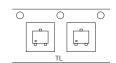


Product & Package Information

• Package : MCPH3

JEITA, JEDEC : SC-70, SOT-323
 Minimum Packing Quantity : 3,000 pcs./reel

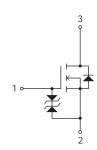
Packing Type: TL



Marking



Electrical Connection

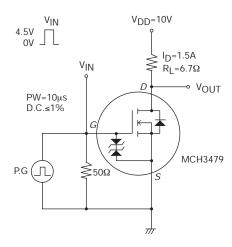


MCH3479

Electrical Characteristics at Ta=25°C

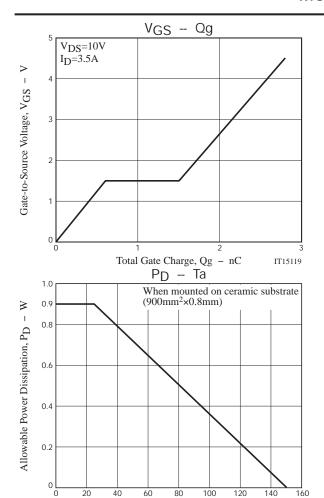
Parameter	Cumbal	Conditions	Ratings			Unit
Parameter	Symbol	Conditions	min	typ	max	UIIII
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	V _{GS} (off)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1.5A		2.8		S
	R _{DS} (on)1	I _D =1.5A, V _{GS} =4.5V		49	64	mΩ
Static Drain-to-Source On-State Resistance	R _{DS} (on)2	I _D =1A, V _{GS} =2.5V		68	95	mΩ
	R _{DS} (on)3	I _D =0.5A, V _{GS} =1.8V		99	149	mΩ
Input Capacitance	Ciss			260		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		65		pF
Reverse Transfer Capacitance	Crss			50		pF
Turn-ON Delay Time	t _d (on)			6.2		ns
Rise Time	t _r	Consider the Action with		19		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		30		ns
Fall Time	t _f			28		ns
Total Gate Charge	Qg			2.8		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =3.5A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd]		0.9		nC
Diode Forward Voltage	V _{SD}	I _S =3.5A, V _{GS} =0V		0.85	1.2	V

Switching Time Test Circuit



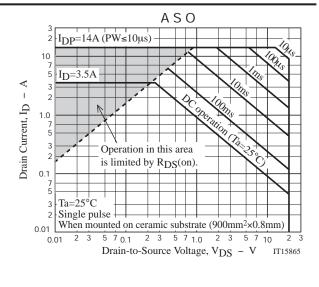
Ordering Information

Device	Package	Shipping	memo
MCH3479-TL-H	MCPH3	3,000pcs./reel	Pb Free and Halogen Free



Ambient Temperature, Ta - °C

IT15866

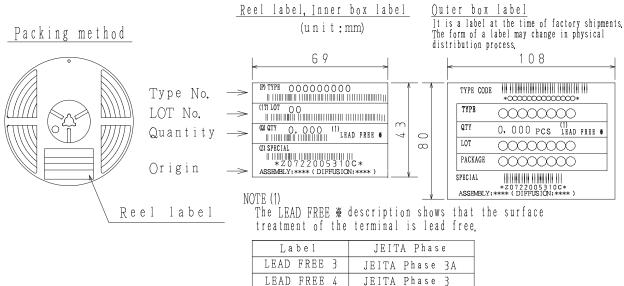


Taping Specification

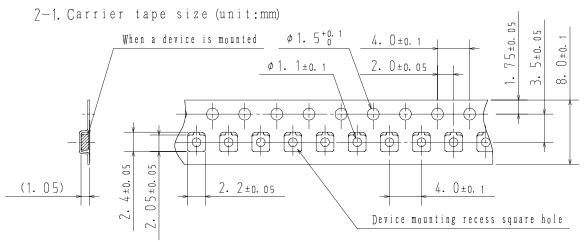
MCH3479-TL-H

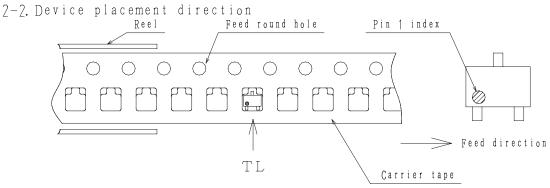
1. Packing Format

Package Name	Carrier Tape	Maximun Number of devices contained (pcs)			Packing	format		
	Туре	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)		
мсрн3	мсрн3	3,000	15, 000	90,000	5 reels contained	6 inner boxes contained		
					Dimensions:mm (external)	Dimensions:mm (external)		
					183×72×185	440×195×210		



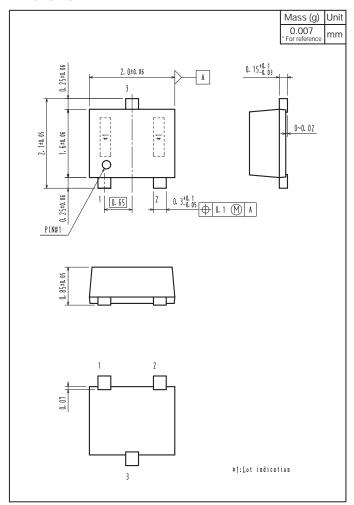
2. Taping configuration



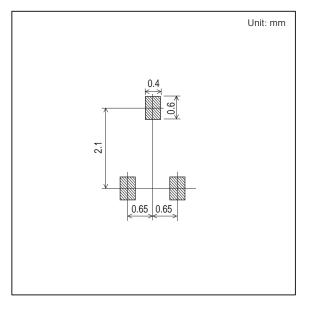


Those with pin 1 index on the feed hole side·····TL

Outline Drawing MCH3479-TL-H



Land Pattern Example



Note on usage: Since the MCH3479 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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